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Amend

a pinned ferromagnetic layer over the non-magnetic conductor spacer layer ;

and

a pinning material layer over the pinned ferromagnetic layer; and

a capping layer over said pinning material layer.

Please add new claims as follows:

33. (new) The method of claim 1 which further includes said seed layer formed of a selected from the group consisting of nickel chromium alloys, nickel -chromium-copper alloys and nickel-iron-chromium alloys.

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34. (new) The method of claim 1 wherein said metal oxide buffer layer comprised of NiO or alpha Fe₂O₃.

35. (new) The method of claim 1 wherein said metal oxide buffer layer comprised of NiO or alpha Fe₂O₃; and said free ferromagnetic layer is comprised of a material selected from the group consisting of: CoFe, CoFe/NiFe, and Co/NiFe

36. (new) The spin valve giant magnetoresistance sensor of claim 18 wherein said seed layer being formed of a material selected from the group consisting of nickel chromium alloys, nickel -chromium-copper alloys and nickel-iron-chromium alloys.
